

TSMC-01-617



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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/074,881 02/12/02

Jiann-Tyng Tzeng et al.

A NOVEL METHOD TO MONITOR PROCESS
CHARGING EFFECT

Grp. Art Unit: 2815

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on May 14, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 5/14/02

U.S. Patent 6,232,134 to Farber et al., "Method and Apparatus for Monitoring Wafer Characteristics and/or Semiconductor Processing Consistency Using Wafer Charge Distribution Measurements," reveals a wafer charge monitoring method.

U.S. Patent 6,060,329 to Kamata et al., "Method for Plasma Treatment and Apparatus for Plasma Treatment," discloses a method for plasma treatment which effects detection of the amount of particles in a plasma generation area.

U.S. Patent 5,861,634 to Hsu et al., "Charge Collector Structure for Detecting Radiation Induced Charge During Integrated Circuit Processing," discloses a method and structure for the evaluation of the density of charge induced to a semiconductor substrate.

U.S. Patent 6,143,579 to Chang et al., "Efficient Method for Monitoring Gate Oxide Damage Related to Plasma Etch Chamber Processing History," discloses the degradation of thin gate oxides caused by plasma processing of polysilicon gate field effect transistors.

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U.S. Patent 5,907,764 to Lowell et al., "In-Line Detection and Assessment of Net Charge in PECVD Silicon Dioxide (Oxide) Layers," discloses a charge monitor and process.

Sincerely,

A handwritten signature consisting of stylized initials and a surname.

Stephen B. Ackerman,
Reg. No. 37761